2SC2315
2SC2316

Silicon NPN Triple Diffused Mesa

☆Super Beta Transistor

Application Example :	● Outline Drawing 1 ·····MT-25(TO220)
General Purpose	

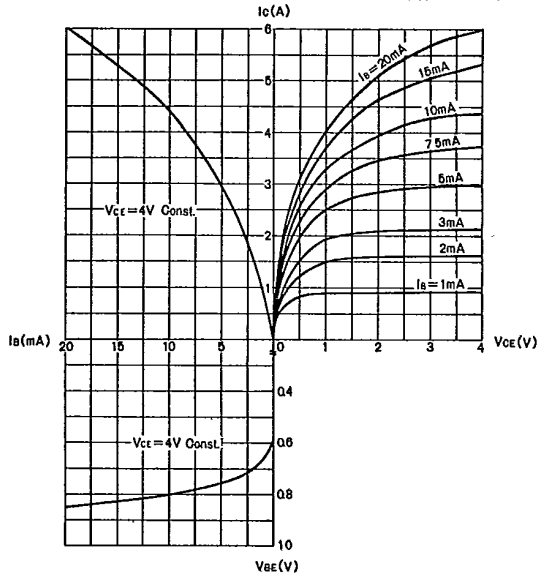
Absolute Maximum Ratings

Symbol	2SC2315	2SC2316	Unit
V_{CBO}	80	100	V
V_{CEO}	60	80	V
V_{EBO}	6		V
I_C	6		A
I_B	3		A
P_C	50 (T_{FL}=25°C)		W
T_j	150		°C
T_{stg}	−55～+150		°C

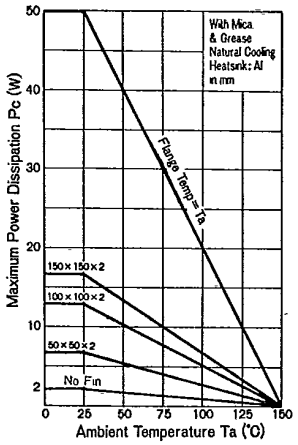
Electrical Characteristics

Symbol	Conditions	2SC2315	2SC2316	Unit
I_{CBO}		100max	100max	μA
	V_{CB}=	80	100	V
I_{EBO}	V_{EB}=6V	1.0max		mA
$V_{(BR)CEO}$	I_C =25mA	60min	80min	V
h_{FE}	V_{CE}=4V, I_C=0.5A	500min		
$V_{CE(sat)}$	I_C =3A, I_B=0.06A	1.0max		V
f_T	V_{CE}=12V, I_E=−0.5A	30typ		MHz

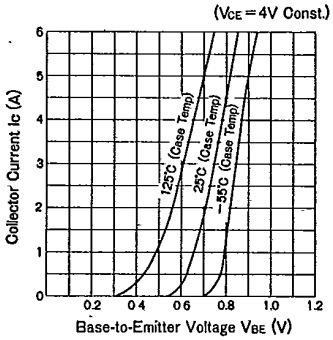
Common Emitter Characteristics (Typical Value)



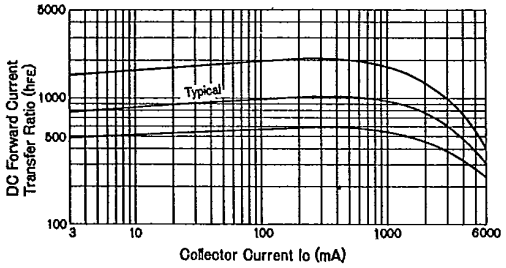
Power Derating



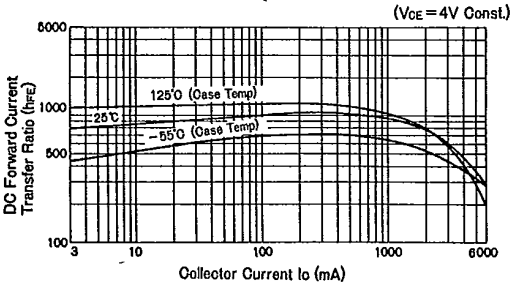
Temperature Characteristics (VCE=4V Const.)



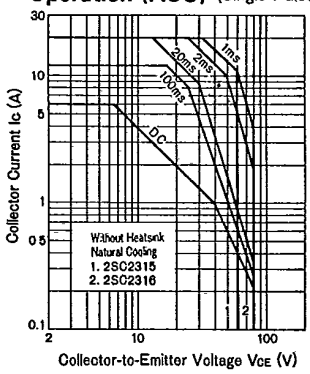
DC Current Gain Characteristics (VCE=4V Const.)



DC Current Gain Temperature Characteristics (VCE=4V Const.)



Maximum Areas For Safe Operation (ASO) (Single Pulse)



Collector-to-Emitter Saturation Characteristics (Typical Value)